

1. Scope :

This specification applies to N/P/N silicon zener double diodes chips,
Device NO. SD-00666G

2. Structure :

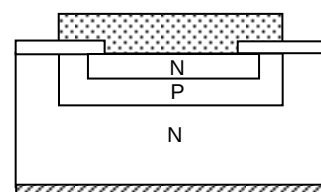
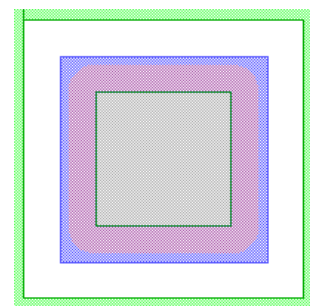
- 2-1. Planar type : N/P/N.
- 2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

3. Size :

- 3-1. ^{※1} Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
- 3-2. Chip thickness : 3.3 ± 0.6 mils (0.085 ± 0.015 mm)
- 3-3. ^{※2} Bonding pad : 4.3 mils x 4.3 mils (0.110 mm x 0.110 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.
^{※1} Including scribing line. The chip size is about $(0.150 \pm 0.015)^2 \text{mm}^2$ after dicing.
^{※2} The wire bonding pad dimension is $(0.110 \pm 0.005)^2 \text{mm}^2$.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Leakage Current	Idf	V=4V Ee=0mW/cm ²			100	nA
	Idr	V=4V Ee=0mW/cm ²			100	
Zener Voltage	Vz(forward)	Izf=5mA Ee=0mW/cm ²	5.5		7.0	V
	Vz(reverse)	Izr=5mA Ee=0mW/cm ²	5.3		6.8	



5. Annotation :

- 5-1. Parallel with one LED
- 5-2. Single pad (one wire bonding applied only)
- 5-3. Double direction Zener diode protection

Equivalent Circuit

